

Spin-on-Glass As-300

Elements of Interest Si, O, As	Key Element atoms/cm³ As, 4E+22	Key Element % in Film Arsenic
Viscosity, n (635nm) 1.1 cps, 1.50	Thickness Coats 3000 Å at 3000 rpm	Shelf Life 20°C 3 months 4°C 9 months

Benefits

- Highest arsenic doping level
- Uniform coatings
- High purity materials
- Lower melting point than silica alone
- Stable processing independent of flow rates
- Available with impurity specification < 1 ppm range and also available <50 ppb range

Typical Application

This is a standard silicate arsenic doped glass very typical for semiconductor applications. Begins curing at about 200°C gives a less dense but solid film. It continues to become increasingly stronger as temperature increases to 650°C or higher. We recommend baking at the highest temperature the substrate will see in any post processing. For doping applications the glass is often removed after drive in.

The arsenic in the glass matrix can act as a diffusion barrier to prevent outgassing of dopant material from the substrate.

Packaging

- 240ml
- 500ml
- 1L
- 2.5L
- 4L

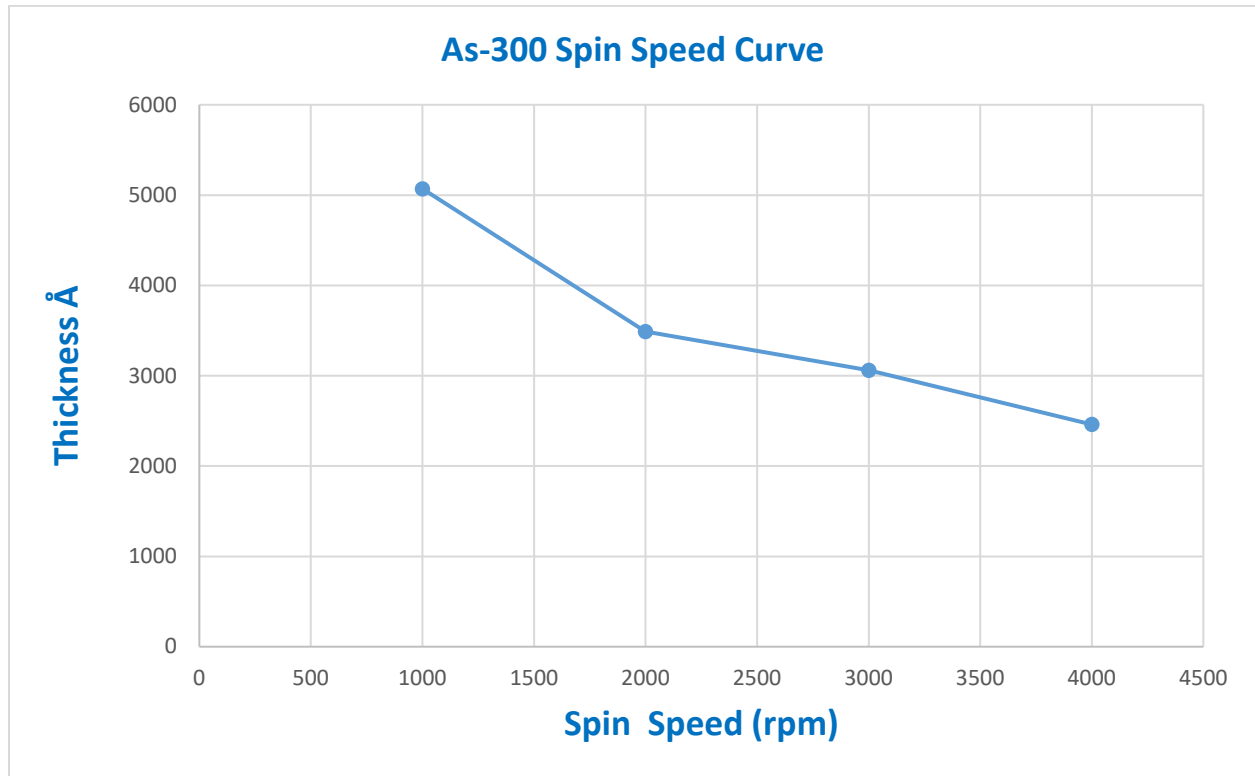
Alternative Products

As-200

Alternate Elements to Add

- Bi
- Sb
- Blends of two or more elements are available
- Other elements available for compound semiconductor use

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